# **BGA416**

RF Cascode Amplifier

**Small Signal Discretes** 



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## **BGA416, RF Cascode Amplifier**

Revision History: 2008-04-21, Rev. 2.1

Previous Version: 2005-07-26

Document layout change
Electrical Characteristics slightly changed
Figures updated

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Data Sheet 3 Rev. 2.1, 2008-04-21



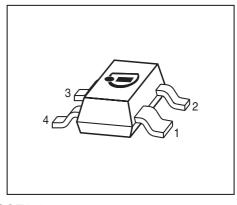
**RF Cascode Amplifier** 

## 1 RF Cascode Amplifier

#### **Feature**

- $G_{MA}$  = 23 dB at 900 MHz
- Ultra high reverse isolation, 60 dB at 900 MHz
- Low noise figure,  $F_{50\Omega}$  = 1.2 dB at 900 MHz
- On chip bias circuitry, 5.5 mA bias current at  $V_{\rm CC}$  = 3 V
- Typical supply voltage: 2.5 to 5.0 V
- SIEGET<sup>®</sup>-25 technology
- · Pb-free (RoHS compliant) package





**SOT143** 

## **Applications**

- · Buffer amplifier
- LNAs
- Oscillator active devices

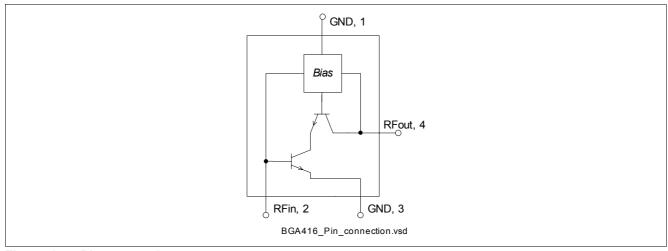


Figure 1 Pin connection

### **Description**

BGA416 is a monolithic silicon cascode amplifier with high reverse isolation. A bias network is integrated for simplified biasing.

Туре	Package	Marking
BGA416	SOT143	C1s

Note: **ESD:** Electrostatic discharge sensitive device, observe handling precaution



#### **Electrical Characteristics**

## **Maximum Ratings**

Table 1 Maximum ratings

Parameter	Symbol Limit Value		Unit		
Voltage at pin RFout	$V_{OUT}$	6	V		
Device current <sup>1)</sup>	$I_{D}$	20	mA		
Current into pin RFin	$I_{in}$	0.5	mA		
Input power	$P_{in}$	8	dBm		
Total power dissipation, $T_{\rm S}$ < 123°C <sup>2)</sup>	$P_{tot}$	100	mW		
Junction temperature	$T_{J}$	150	°C		
Ambient temperature range	$T_{A}$	-65 150	°C		
Storage temperature range	$T_{STG}$	-65 150	°C		

<sup>1)</sup> Device current is equal to current into pin RFout

Note: All Voltages refer to GND-Node

#### Thermal resistance

Table 2 Thermal resistance

Parameter	Symbol	Value	Unit
Junction - soldering point <sup>1)</sup>	$R_{thJS}$	270	K/W

<sup>1)</sup> For calculation of  $R_{\mathrm{thJA}}$  please refer to Application Note Thermal Resistance

## 2 Electrical Characteristics

Electrical characteristics at  $T_{\rm A}$  = 25 °C (measured in test circuit specified in **Figure 2**)  $V_{\rm CC}$  = 3 V, unless otherwise specified

**Table 3** Electrical Characteristics

Parameter	Symbol	Values		Unit	Note /	
		Min.	Тур.	Max.		<b>Test Condition</b>
Maximum available power gain	$G_{MA}$		23		dB	f = 0.9 GHz
			14		dB	f = 1.8 GHz
Insertion power gain	$ S_{21} ^2$		17		dB	f = 0.9 GHz
			11		dB	f = 1.8 GHz
Reverse isolation	$ S_{12} $		60		dB	f = 0.9 GHz
			40		dB	f = 1.8 GHz
Noise figure ( $Z_{\rm S}$ = 50 $\Omega$ )	$F_{50\Omega}$		1.2		dB	f = 0.9 GHz
			1.6		dB	f = 1.8 GHz
Output power at 1 dB gain compression ( $Z_{\rm S}$ = $Z_{\rm L}$ = 50 $\Omega$ )	$P_{ ext{-1dB}}$		-3		dBm	f = 0.9 GHz
			-3		dBm	f = 1.8 GHz
Output third order intercept point $(Z_{\rm S} = Z_{\rm L} = 50 \ \Omega)$	OIP <sub>3</sub>		14		dBm	f = 0.9 GHz
			14		dBm	f = 1.8 GHz
Device current	$I_{D}$		5.5		mA	

<sup>2)</sup>  $T_{\rm S}$  is measured on the ground lead at the soldering point



## **Electrical Characteristics**

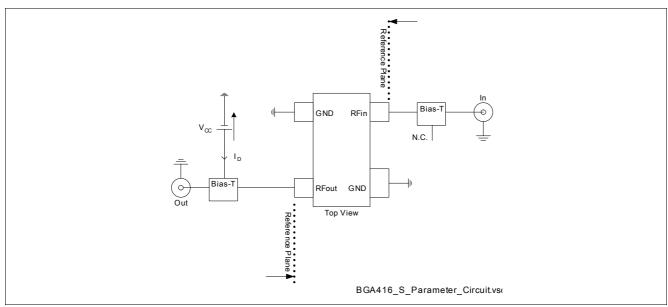


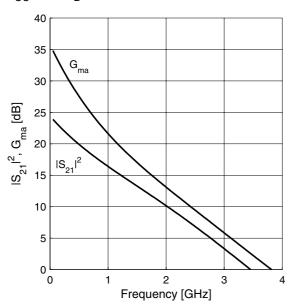
Figure 2 Test Circuit for Electrical Characteristics



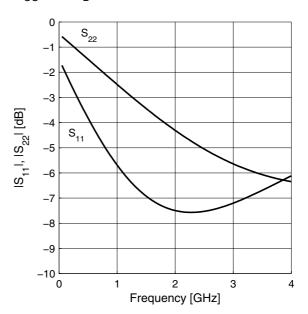
**Measured Parameters** 

## **3** Measured Parameters

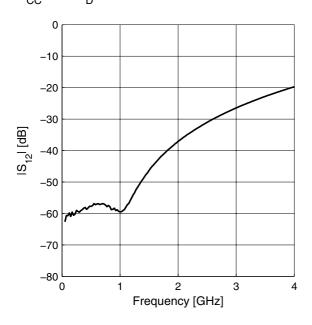
**Power Gain** 
$$|S_{21}|^2$$
,  $G_{ma} = f(f)$   
 $V_{CC} = 3V$ ,  $I_D = 5.5mA$ 



$$\begin{aligned} & \textbf{Matching} \ |S_{11}|, \ |S_{22}| = f(f) \\ & V_{CC} = 3V, \ I_D = 5.5 mA \end{aligned}$$

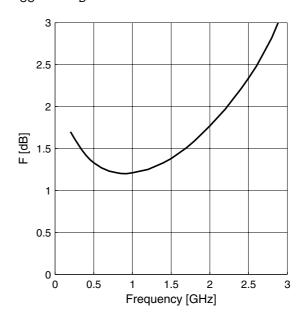


Reverse Isolation 
$$|S_{12}| = f(f)$$
  
 $V_{CC} = 3V$ ,  $I_D = 5.5mA$ 



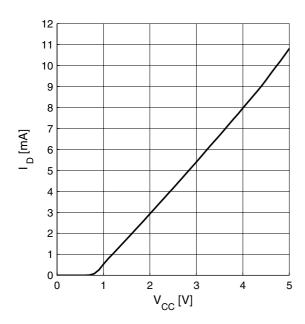
Noise figure 
$$F = f(f)$$

$$V_{CC} = 3V, I_{D} = 5.5 \text{mA}$$



**Package Information** 

# **Device Current** $I_D = f(V_{CC})$



# 4 Package Information

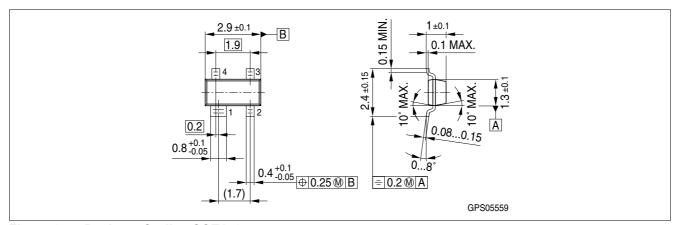


Figure 3 Package Outline SOT143

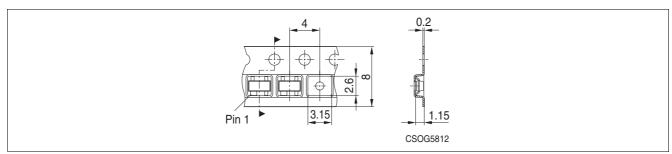


Figure 4 Tape for SOT143

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